Search History

L Number	Hits	Search Text	DB	Time stamp
1	311608	nonvolatile or eeprom or flash	USPAT;	2004/06/03
		-	US-PGPUB;	08:43
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
2	40615	sense near2 amplifier	USPAT;	2004/06/03
			US-PGPUB;	08:43
			EPO; JPO;	
			DERWENT;	
_			IBM_TDB	2224/25/22
3	1093170	program\$4	USPAT;	2004/06/03
			US-PGPUB;	08:44
			EPO; JPO;	
			DERWENT;	
4	70103	(hit was line) on hitling	IBM_TDB USPAT;	2004/06/03
4	70103	(bit near line) or bitline	US-PGPUB;	08:45
			EPO; JPO;	08:45
			DERWENT;	
			IBM TDB	
5	23046	select\$4 near2 transistor	USPAT;	2004/06/03
~	23040	DOLOGOY I MOULE CLUMDISCOL	US-PGPUB;	08:45
			EPO; JPO;	
			DERWENT;	
			IBM TDB	
6	66737	program\$4 near2 operation	USPAT;	2004/06/03
•		F3	US-PGPUB;	08:46
			EPO; JPO;	
			DERWENT;	
			IBM TDB	
7	26336	(program\$4 near2 operation) with	USPAT;	2004/06/03
		control\$4	US-PGPUB;	08:46
			EPO; JPO;	
			DERWENT;	
		·	IBM_TDB	
8	1397594	"one time" or once	USPAT;	2004/06/03
			US-PGPUB;	08:46
			EPO; JPO;	
			DERWENT;	
^	100665	(1)	IBM_TDB	2004/05/02
9	103665	,	USPAT;	2004/06/03
		execut\$3)	US-PGPUB;	08:47
			EPO; JPO; DERWENT;	
			IBM TDB	
10	8216	cell near9 sandwich\$4	USPAT;	2004/06/03
	0210	COLL HORLY SAHAWIOHYT	US-PGPUB;	08:47
			EPO; JPO;	
			DERWENT;	
			IBM TDB	
11	8942	(nonvolatile or eeprom or flash) and	USPAT;	2004/06/03
		(sense near2 amplifier)	US-PGPUB;	08:48
		<u>'</u> '	EPO; JPO;	
			DERWENT;	
			IBM TDB	
12	5782	((nonvolatile or eeprom or flash) and	USPĀT;	2004/06/03
		(sense near2 amplifier)) and program\$4	US-PGPUB;	08:48
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
13	4152	(((nonvolatile or eeprom or flash) and	USPAT;	2004/06/03
		(sense near2 amplifier)) and program\$4)	US-PGPUB;	08:48
		and ((bit near line) or bitline)	EPO; JPO;	
			DERWENT;	
	1		IBM TDB	1

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	14	1750	((((nonvolatile or eeprom or flash) and (sense near2 amplifier)) and program\$4) and ((bit near line) or bitline)) and (select\$4 near2 transistor)	USPAT; US-PGPUB; EPO; JPO; DERWENT;	2004/06/03 08:48
	15	973	<pre>(((((nonvolatile or eeprom or flash) and (sense near2 amplifier)) and program\$4) and ((bit near line) or bitline)) and (select\$4 near2 transistor)) and</pre>	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2004/06/03 08:48
	16	525	<pre>(program\$4 near2 operation) ((((((nonvolatile or eeprom or flash) and (sense near2 amplifier)) and program\$4) and ((bit near line) or bitline)) and (select\$4 near2 transistor)) and (program\$4 near2 operation)) and</pre>	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/03 08:48
-	17	342	<pre>and (sense near2 amplifier)) and program\$4) and ((bit near line) or bitline)) and (select\$4 near2 transistor)) and (program\$4 near2</pre>	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/03 08:48
1	18	95	operation)) and ((program\$4 near2 operation) with control\$4)) and ("one time" or once) ((((((((nonvolatile or eeprom or flash) and (sense near2 amplifier)) and program\$4) and ((bit near line) or bitline)) and (select\$4 near2 transistor)) and (program\$4 near2 operation)) and ((program\$4 near2	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/03 08:49
]	19	10	operation) with control\$4)) and ("one time" or once)) and (("one time" or once) with (perform\$4 or execut\$3))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/06/03 08:49
			operation)) and ((program\$4 near2 operation) with control\$4)) and ("one time" or once)) and (("one time" or once) with (perform\$4 or execut\$3))) and (cell near9 sandwich\$4)		